

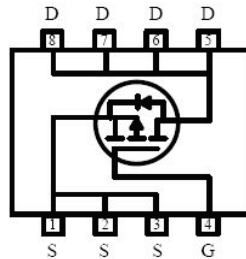
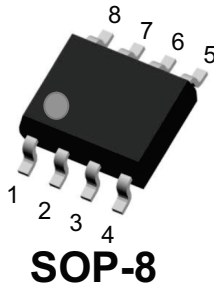


P-Channel Enhancement-Mode MOSFET (-30V, -9.1A)

PRODUCT SUMMARY		
V _{DS}	I _D	R _{DS(on)} (m-ohm) Max
-30V	-9.1A	20 @ V _{GS} = -10V, I _D = -9.1A
		35 @ V _{GS} = -4.5V, I _D = -6.9A

Features

- Advanced Trench Process Technology
- High Density Cell Design for Ultra Low On-Resistance
- Lead free product is acquired
- Surface mount Package
- Ordering information : KF4435 (Lead (Pb) -free)
KF4435-G (Lead (Pb) -free and halogen-free)

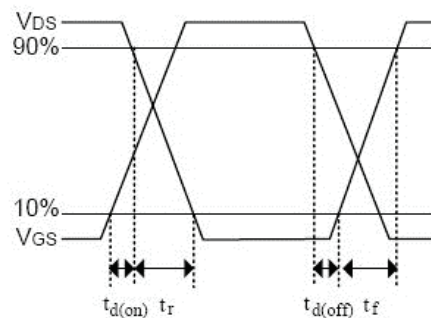
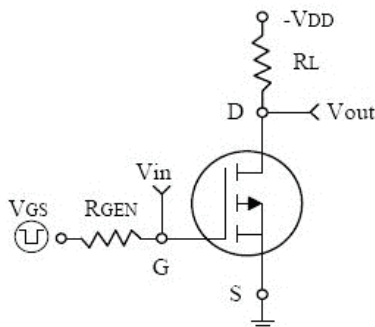


Pin 1 / 2 / 3: Source
Pin 4: Gate
Pin 5 / 6 / 7 / 8: Drain

Absolute Maximum Ratings (T_A=25°C, unless otherwise noted)

Symbol	Parameter	Ratings	Units
V _{DS}	Drain-Source Voltage	-30	V
V _{GS}	Gate-Source Voltage	±20	V
I _D	Drain Current (Continuous)	-9.1	A
I _{DM}	Drain Current (Pulsed) ^a	-36	A
P _D	Total Power Dissipation @T _A =25°C	2.5	W
I _S	Maximum Diode Forward Current	-2.1	A
T _j , T _{stg}	Operating Junction and Storage Temperature Range	-55 to +150	°C
R _{θJA}	Thermal Resistance Junction to Ambient (PCB mounted) ^b	50	°C/W

a: Repetitive Rating: Pulse width limited by the maximum junction temperature.
b: 1-in² 2oz Cu PCB board



Switching Test Circuit and Switching Waveforms